

ABSTRACT

[00122] A method and apparatus for monitoring an etch process. The etch process may be monitored using measurement information (e.g., critical dimensions (CD), layer thickness, and the like) provided ex-situ with respect to the etch process in combination with in-situ monitoring (e.g., spectroscopy, interferometry, scatterometry, reflectometry, and the like) performed during the etch process. The ex-situ measurement information in combination with the in-situ monitoring may be used to monitor for example, an endpoint of an etch process, an etch depth profile of a feature formed on a substrate, fault detection of an integrated circuit manufacturing process, and the like.